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Team Nexperia



High-speed USB OTG ESD protection diode arrays Rev. 3 — 14 June 2012

Product data sheet

Product profile

1.1 General description

PUSBMxX4-TL is a series of four 4-channel ElectroStatic Discharge (ESD) diode arrays for USB 2.0 (On-The-Go (OTG)) interfaces. The devices provide protection to downstream components from ESD voltages up to ±8 kV contact discharge. They offer three low capacitance ESD protection pins and one V_{BUS} protection diode. They are encapsulated in an ultra thin DFN1616-6 (SOT1189-1/XSON6) plastic package with 0.5 mm pitch. These features make the devices ideal for use in applications requiring component miniaturization, such as mobile phone handsets.

1.2 Features and benefits

- Pb-free, Restriction of Hazardous Substances (RoHS) and Dark Green compliant
- ESD protection according to IEC 61000-4-2 level 4: ±8 kV contact discharge
- Electrical Fast Transients (EFT) protection according to IEC 61000-4-4 40A (5/50 ns)
- Three pairs of ultra low capacitance (1.1 pF typ.) rail-to-rail ESD protection diodes
- Ultra thin DFN1616-6 (SOT1189-1/XSON6) plastic package; 0.5 mm pitch

1.3 Applications

High-speed USB 2.0 and USB OTG connector ESD protection in:

- Cellular phone and Personal Communication System (PCS) mobile handsets
- Mobile internet devices
- Digital still cameras
- Portable media players

Pinning information

Table 1. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	low capacitance ESD protection		
2	low capacitance ESD protection	6 5 4	
3	low capacitance ESD protection		$\begin{array}{c ccccccccccccccccccccccccccccccccccc$
4	not connected	7	\uparrow \downarrow \downarrow \uparrow
5	not connected		
6	V _{BUS} ESD protection		center pad
7	ground (GND)	Transparent top view	018aaa140



3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
PUSBM5V5X4-TL	DFN1616-6	plastic, thermal enhanced extremely thin small outline package; no leads; 6 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT1189-1		
PUSBM12VX4-TL					
PUSBM15VX4-TL					
PUSBM30VX4-TL					

4. Marking

Table 3. Marking codes

Type number	Marking code
PUSBM5V5X4-TL	XE
PUSBM12VX4-TL	XL
PUSBM15VX4-TL	XO
PUSBM30VX4-TL	30

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RWM}	reverse standoff voltage	pins 1, 2, 3	-0.5	+5.5	V
	PUSBM5V5X4-TL	pin 6 (V _{BUS})	-0.5	+5.5	V
	PUSBM12VX4-TL	pin 6 (V _{BUS})	-0.5	+12	V
	PUSBM15VX4-TL	pin 6 (V _{BUS})	-0.5	+15	V
	PUSBM30VX4-TL	pin 6 (V _{BUS})	-0.5	+30	V
V _{ESD}	electrostatic discharge voltage	IEC 61000-4-2, level 4; pins 1, 2, 3, 6 to GND; contact discharge	[1] -	±8	kV
P _{PP}	peak pulse power	t _p = 8/20 μs			
		pins 1, 2, 3; V _{CL} = 12 V	-	35	W
	PUSBM5V5X4-TL	pin 6 (V_{BUS}); $V_{CL} = 9.2 \text{ V}$	-	100	W
	PUSBM12VX4-TL	pin 6 (V_{BUS}); $V_{CL} = 16 \text{ V}$	-	100	W
	PUSBM15VX4-TL	pin 6 (V_{BUS}); $V_{CL} = 22 \text{ V}$	-	100	W
	PUSBM30VX4-TL	pin 6 (V_{BUS}); $V_{CL} = 43 \text{ V}$	-	100	W
I_{PP}	peak pulse current	t _p = 8/20 μs			
		pins 1, 2, 3	-	3	Α
	PUSBM5V5X4-TL	pin 6 (V _{BUS})	-	12	Α
	PUSBM12VX4-TL	pin 6 (V _{BUS})	-	6	Α
	PUSBM15VX4-TL	pin 6 (V _{BUS})	-	3	Α
	PUSBM30VX4-TL	pin 6 (V _{BUS})	-	2	Α

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High-speed USB OTG ESD protection diode arrays

 Table 4.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$T_{reflow(peak)}$	peak reflow temperature	$t_p \le 10 \text{ s}$	-	+260	°C
T _{amb}	ambient temperature		-30	+85	°C
T _{stg}	storage temperature		-55	+150	°C

^[1] Device is qualified with 1000 pulses of ±8 kV contact discharges each, according to IEC61000-4-2 far exceeding level 4 (±8 kV contact discharge).

6. Characteristics

Table 5. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		0.6	-	1.2	V
Low capaci	tance ESD protection					
V_{BRzd}	Zener diode breakdown voltage	$I_{test} = 1 \text{ mA}$	6	-	10	V
$C_{(I/O\text{-}GND)}$	input/output to ground capacitance	$V_{bias(DC)} = 0.5 \text{ V; f} = 1 \text{ MHz;}$ pins 1, 2, 3 to GND	<u>[1]</u> _	1.1	1.3	pF
$\Delta C_{(I/O\text{-}GND)}$	input/output to ground capacitance variation	$V_{bias(DC)} = 0.5 \text{ V}; f = 1 \text{ MHz}$	-	0.02	-	pF
$C_{(I/O-I/O)}$	input/output to input/output capacitance	$V_{bias(DC)} = 0.5 \text{ V; } f = 1 \text{ MHz;}$ pins 1 to 2, 1 to 3, 2 to 3	-	0.5	-	pF
I _{RM}	reverse leakage current	pins 1, 2, 3 to GND; $V_{RWM} = 5.5 \text{ V}$	-	100	1000	nA
V _{BUS} ESD p	rotection					
V_{BR}	breakdown voltage	pin 6 (V_{BUS}) to GND; $I_{test} = 1 \text{ mA}$				
	PUSBM5V5X4-TL		6.4	6.8	7.2	V
	PUSBM12VX4-TL		12.5	14.5	16	V
	PUSBM15VX4-TL		17	18	19	V
	PUSBM30VX4-TL		32	36	40	V
C _d	diode capacitance	$V_{bias(DC)} = 0.5 \text{ V; } f = 1 \text{ MHz;}$ pin 6 (V_{BUS}) to GND				
	PUSBM5V5X4-TL		-	165	220	pF
	PUSBM12VX4-TL		-	73	100	pF
	PUSBM15VX4-TL		-	60	90	pF
	PUSBM30VX4-TL		-	50	70	pF
I_{RM}	reverse leakage current	pin 6 (V _{BUS}) to GND				
	PUSBM5V5X4-TL	V _{RWM} = 5.5 V	-	200	500	nA
	PUSBM12VX4-TL	V _{RWM} = 12 V	-	1	100	nA
	PUSBM15VX4-TL	V _{RWM} = 15 V	-	1	100	nA
	PUSBM30VX4-TL	$V_{RWM} = 30 \text{ V}$	-	1	100	nA

^[1] Guaranteed by design.

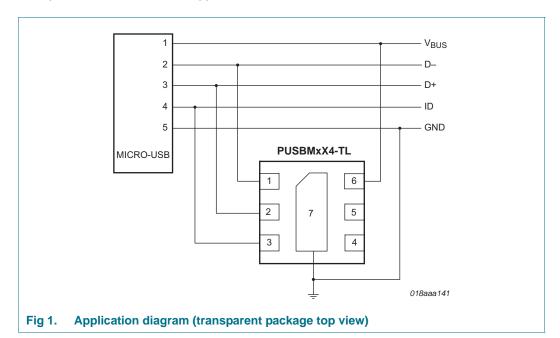
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7. Application information

7.1 Typical application

The devices are designed to protect USB interfaces from downstream ESD. They offer three low capacitance ESD protection channels for D–, D+ and ID and a high-voltage ESD protection channel for V_{BUS} .

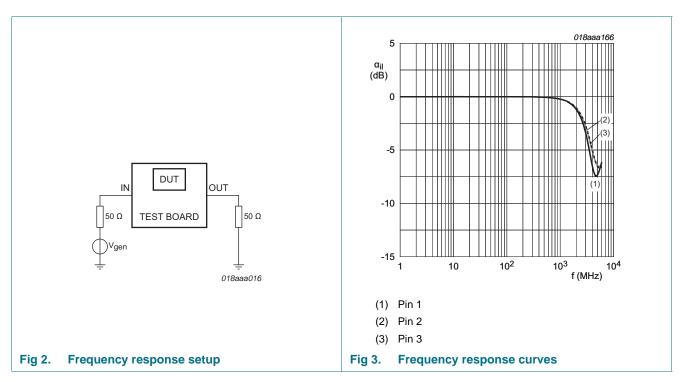


Product data sheet

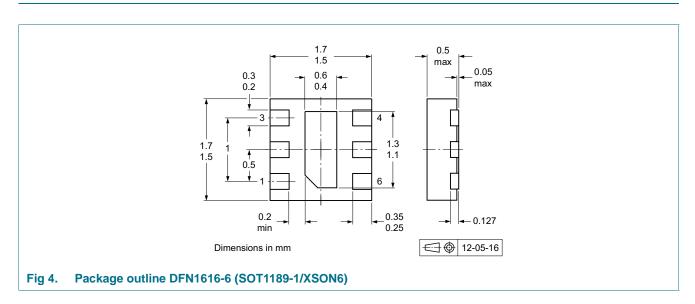
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7.2 Insertion loss

The setup for measuring frequency response curves in a 50 Ω system is shown in <u>Figure 2</u>. The frequency response curves for the low capacitance ESD protection channels (pins 1 to 3) are depicted in <u>Figure 3</u>.



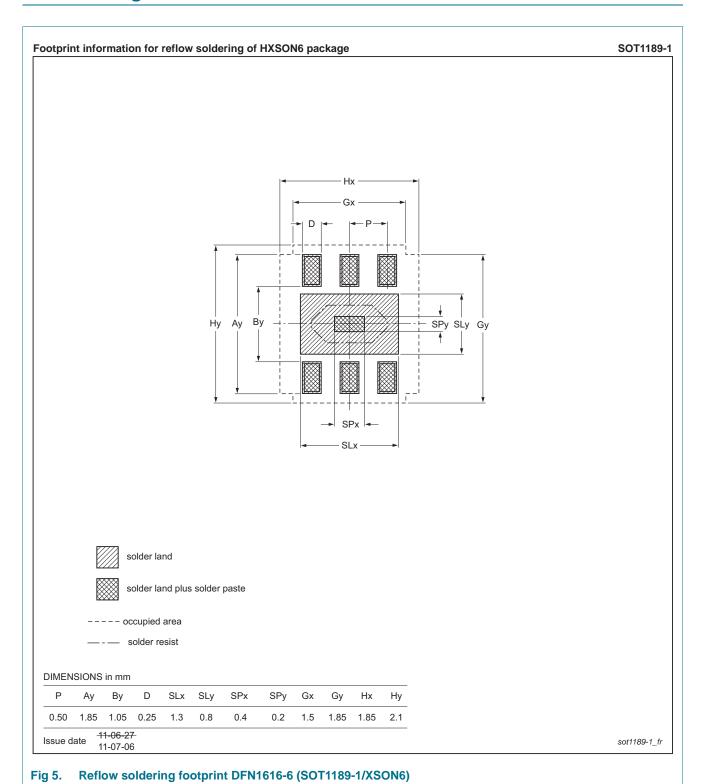
8. Package outline



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9. Soldering



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10. Revision history

Table 6. Revision history

	-			
Document ID Release date		Data sheet status	Change notice	Supersedes
PUSBMXX4-TL_SER v.3	20120614	Product data sheet	-	PUSBMXX4-TL_SER v.2
Modifications:	Section 2 "Pin	ning information": simplific	ed outline graph update	ed
	 Figure 1 upda 	ted		
	 Figure 4 repla 	ced by minimized packag	e outline	
PUSBMXX4-TL_SER v.2	20120416	Preliminary data sheet	-	PUSBMXX4-TL_SER v.1
PUSBMXX4-TL_SER v.1	20111209	Preliminary data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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